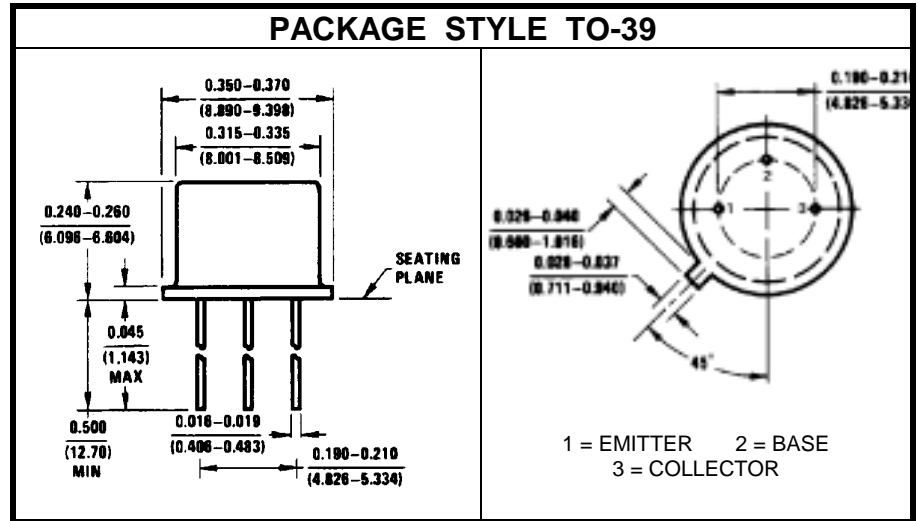


# SILICON NPN RF POWER TRANSISTOR

**DESCRIPTION:** The MRF227 is designed for large signal power amplifier applications operating to 225 MHz

## MAXIMUM RATINGS

$I_C$	0.6 A
$V_{CB}$	36 V
$V_{CE}$	16 V
$P_{DISS}$	8 W @ $T_C = 25^\circ\text{C}$
$T_J$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$



## CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50\text{ mA}$	16			V
$BV_{CES}$	$I_C = 50\text{ mA}$	36			V
$BV_{EBO}$	$I_C = 1.0\text{ mA}$	4.0			V
$I_{CBO}$	$V_{CE} = 15\text{ V}$			1.0	mA
$H_{FE}$	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	20		200	---
$C_{OB}$	$V_{CB} = 12.5\text{ V}$ $f = 1.0\text{ MHz}$			15	Pf
$G_{PE}$	$P_{OUT} = 3.0\text{ W}$ $V_{CE} = 12.5\text{ V}$ $f = 225\text{ MHz}$	13.5	15		dB
$\eta$	$P_{OUT} = 3.0\text{ W}$ $V_{CE} = 12.5\text{ V}$ $f = 225\text{ MHz}$	60			%